International IOR Rectifier

HFA04SD60S

Ultrafast, Soft Recovery Diode

Features

- · Ultrafast Recovery Time
- · Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- · Guaranteed Avalanche
- · Specified at Operating Temperature

Benefits

- · Reduced RFI and EMI
- · Reduced Power Loss in Diode and **Switching Transistor**
- · Higher Frequency Operation
- · Reduced Snubbing
- · Reduced Parts Count

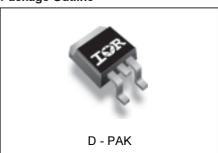
Description/ Applications

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

 $t_{rr} = 38ns$ $I_{F(AV)} = 4Amp$

 $V_{R} = 600V$

Package Outline



Absolute Maximum Ratings

	Parameters	Max	Units
V _{RRM}	Cathode-to-Anode Voltage	600	V
I _{F(AV)}	Continuous Forward Current	4	A
	$T_C = 100$ °C		
I _{FSM}	Single Pulse Forward Current	25	
I _{FRM}	Peak Repetitive Forward Current	16	
	$T_{C} = 116^{\circ}C$		
P_D	Maximum Power Dissipation	10	W
	$T_{C} = 100^{\circ}C$		
T _J , T _{STG}	Operating Junction and Storage Temperatures	- 55 to 150	°C

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Bulletin PD-20617 rev. D 10/06



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameters	Min	Тур	Max	Units	Test Conditions
V_{BR}, V_{r}	Breakdown Voltage, Blocking Voltage	600	-	-	V	Ι _R = 100μΑ
V _F	Forward Voltage	-	1.5	1.8	٧	I _F = 4A
	See Fig. 1	1	1.8	2.2	V	I _F = 8A
		-	1.4	1.7	V	I _F = 4A, T _J = 125°C
I _R	Max. Reverse Leakage Current	-	0.17	3.0	μA	$V_R = V_R$ Rated
		-	44	300	μA	$T_J = 125^{\circ}C$, $V_R = 0.8 \times V_R$ Rated
C _T	Junction Capacitance	-	4	8	pF	V _R = 200V
Ls	Series Inductance	-	8.0	-	nH	Measured lead to lead 5mm from package body

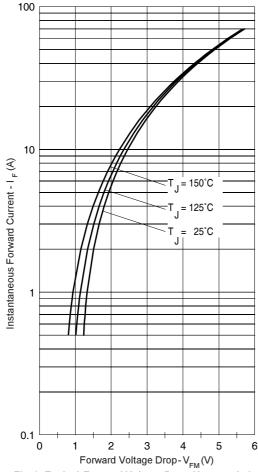
Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

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	Parameters	Min	Тур	Max	Units	Test Conditions	S
t _{rr}	Reverse Recovery Time	-	17	-	ns	$I_F = 1.0A$, $di_F/dt = 2$	200A/µA, V _R = 30V
		-	28	42		T _J = 25°C	I _F =4A
		•	38	57		T _J = 125°C	V _R = 200V
I _{RRM}	Peak Recovery Current	-	2.9	5.2	Α	T _J = 25°C	di _F /dt = 200A/µs
		-	3.7	6.7		T _J = 125°C	
Q _{rr}	Reverse Recovery Charge	-	40	60	nC	T _J = 25°C	
		-	70	105		T _J = 125°C	
di _{(rec)M} /dt	Rate of Fall of recovery Current	-	280	-	A/µs	T _J = 25°C	
		-	235	-		T _J = 125°C	

Thermal - Mechanical Characteristics

	Parameters	Min	Тур	Max	Units
TJ	Max. Junction Temperature Range	-	-	- 55 to 150	°C
T _{Stg}	Max. Storage Temperature Range	-	-	- 55 to 150	
Ts	Soldering Temperature, 10 sec	-	-	240	
R_{thJC}	Thermal Resistance, Junction to Case	-	-	5.0	°C/W
R _{thJA} ①	Thermal Resistance, Junction to Ambient	-	-	80	
VVt	Weight	-	2.0	-	g
		-	0.07	-	(oz)
Т	Mounting Torque	6.0	-	12	Kg*cm
		5.0	-	10	lbf*in

① Typical Socket Mount



1000 T_J = 150°C 100 Reverse Current - I R (µA) 125°C 10 -25°C 0.1 0.01 0.001 100 200 300 400 500 Reverse Voltage- $V_R(V)$

Fig. 2-Typical Values Of Reverse Current Vs. Reverse Voltage

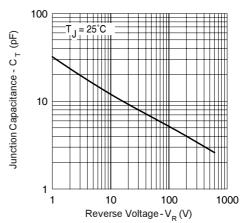


Fig. 1-Typical Forward Voltage Drop Characteristics



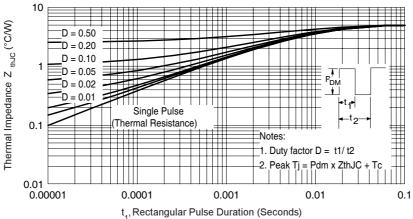
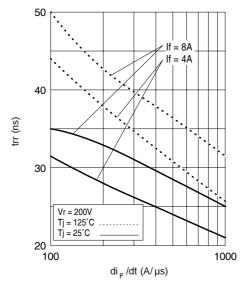


Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics



 $Fig.\,5-Typical\,Reverse\,Recovery\,\,vs.\,di_{_F}/dt$

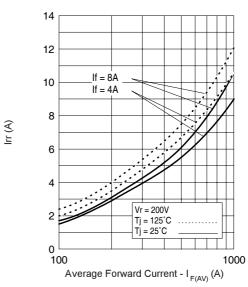


Fig. 6 - Typical Recovery Current vs. di $_{\rm F}/{\rm dt}$

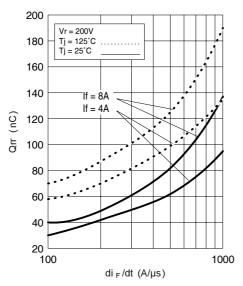


Fig. 7 - Typical Stored Charge vs. di _F/dt

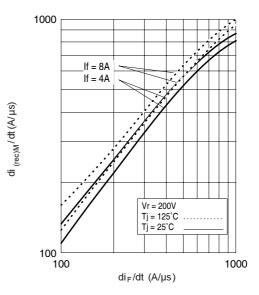


Fig. 8 - Typical di $_{(rec)M}/dt$ vs. di $_F/dt$

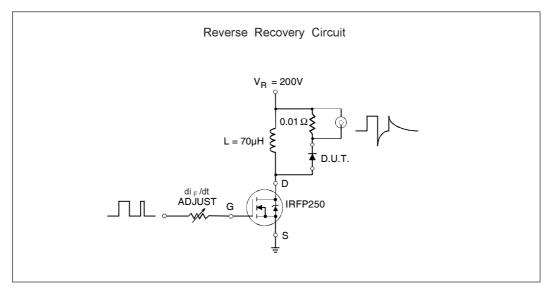


Fig. 9- Reverse Recovery Parameter Test Circuit

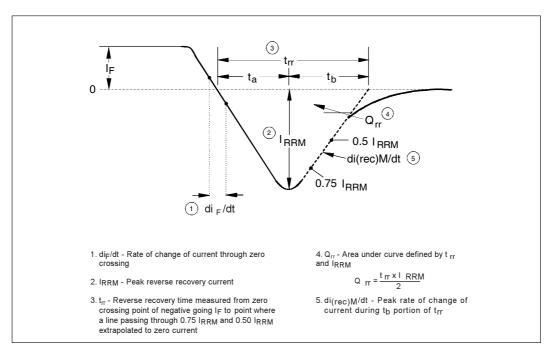
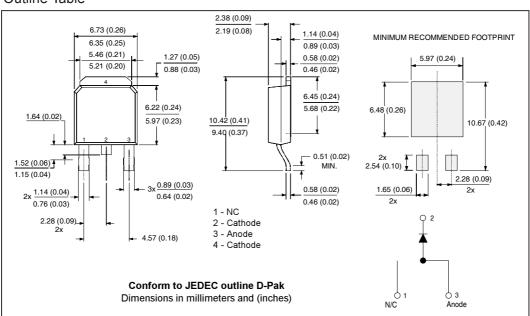


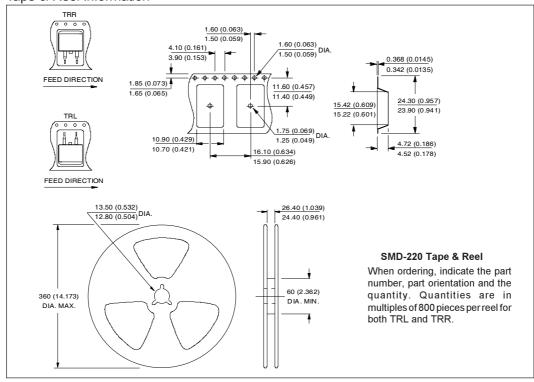
Fig. 10 - Reverse Recovery Waveform and Definitions

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Outline Table



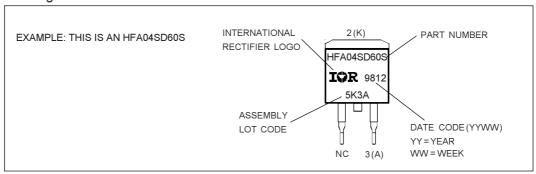
Tape & Reel Information



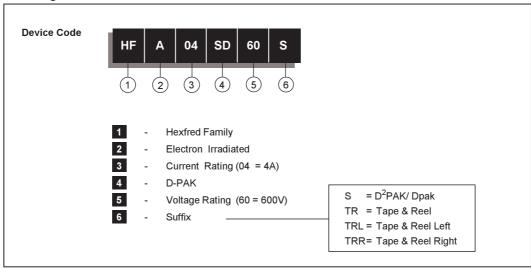
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Marking Information



Ordering Information Table



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